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Abstract

Semiconductor component with integrated capacitance structure, and method for fabrication thereof

A semiconductor component has an insulating layer which is formed on a semiconductor substrate and in which a capacitance structure (K) is formed. The capacitance structure (K) has at least two metallization planes (1 to 7) which are arranged parallel to one another and are each connected to an electrical connecting line. Arranged between the metallization planes (1 to 7) is at least one electrically conductive region (1a to 1j; 2a to 2j; 31a to 36a; 41a to 46a; 5a to 5f) for producing a capacitance surface, the electrically conductive region (1a to 1j; 2a to 2j; 31a to 36a; 41a to 46a; 5a to 5f) being electrically connected only to one of the metallization planes (1 to 7)..

(Figure 1)